SKKE 1200

SEMIPACK® 6

Rectifier Diode Modules

SKKE 1200

Features

- Precisious metal pressure contacts for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- Rectifiers

V_{RSM} V	V_{RRM} V	I_{FRMS} = 2000 A (maximum value for continuous operation) I_{FAV} = 1180 A (sin. 180; T_c = 100 °C)		
1900	1800	SKKE 1200/18 H4		
2200	2200	SKKE 1200/22 H4		

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; T_c = 100 °C	1180	A
I_{FSM}	T_{vj} = 25 °C; 10 ms	45000	A
	T_{vj} = 160 °C; 10 ms	40000	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	10125000	A²s
	T_{vj} = 160 °C; 8,3 ... 10 ms	8000000	A²s
V_F	T_{vj} = 25 °C; I_F = 3000 A	max. 1,4	V
$V_{(TO)}$	T_{vj} = 160 °C	max. 0,72	V
r_T	T_{vj} = 160 °C	max. 0,19	mΩ
I_{RD}	T_{vj} = 160 °C; V_{RD} = V_{RRM}	max. 60	mA
$R_{th(j-c)}$	cont.	0,0385	K/W
	sin. 180	0,04	K/W
$R_{th(c-s)}$		0,01	K/W
T_{vj}		- 40 ... + 160 [1)]	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	6 ± 15%	Nm
M_t	to terminals	18 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	2150	g
Case		A82	

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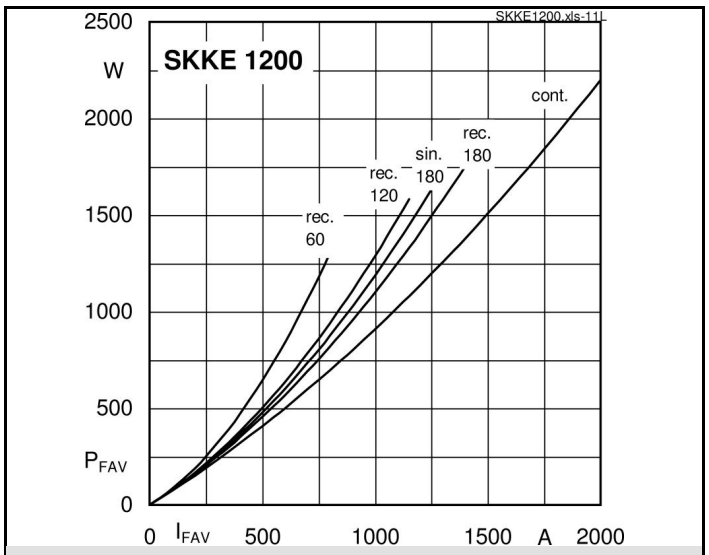


Fig. 11L Power dissipation per diode vs. forward current

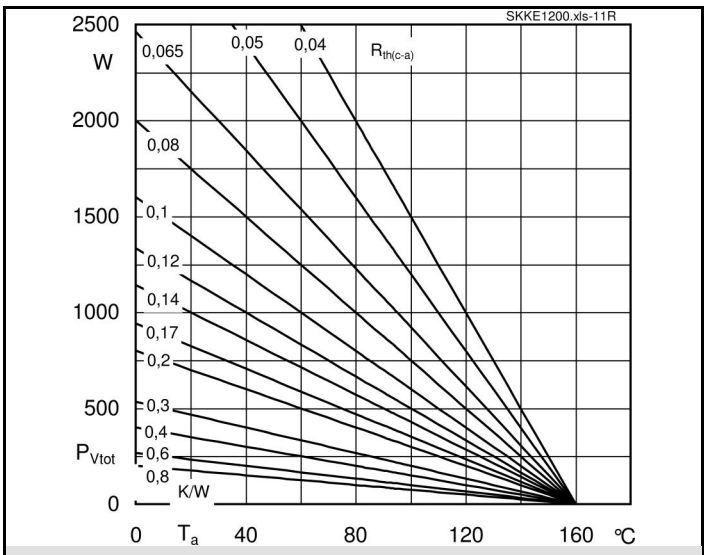


Fig. 11R Power dissipation per diode vs. ambient temperature

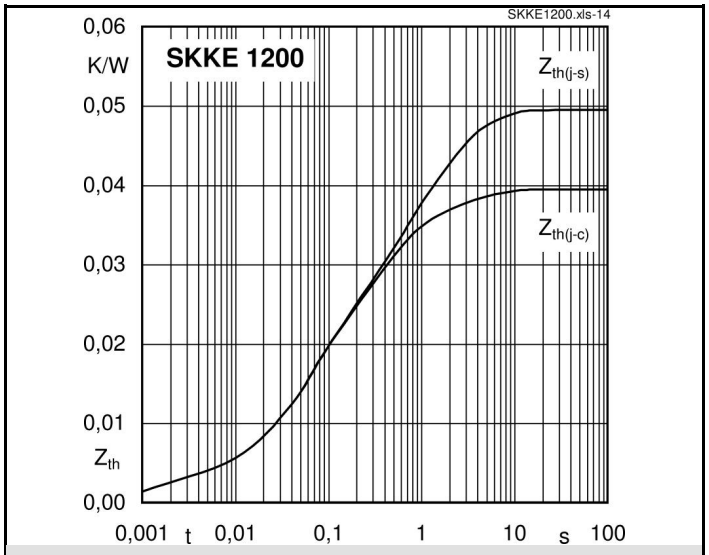


Fig. 14 Transient thermal impedance vs. time

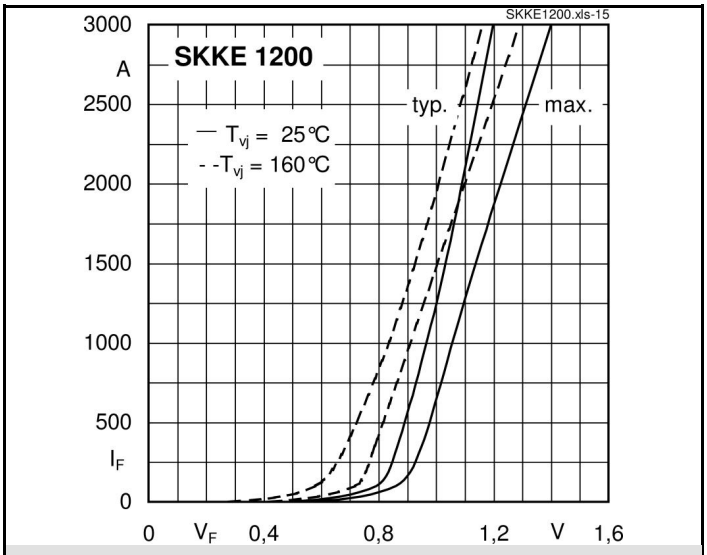


Fig. 15 Forward characteristics

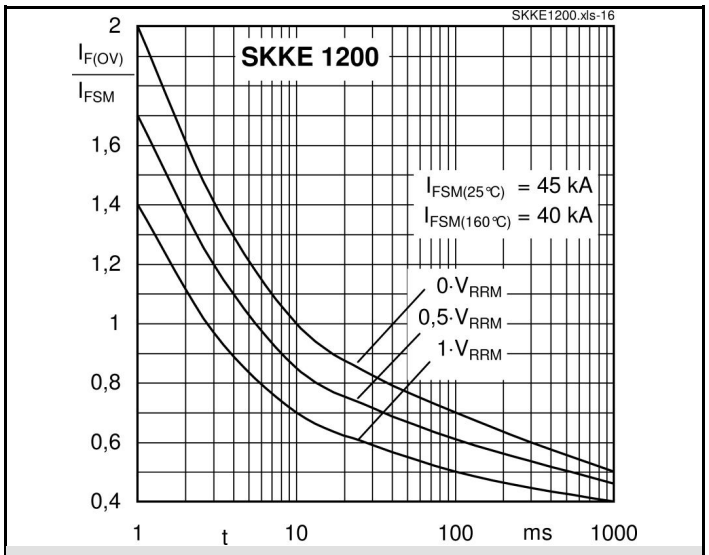
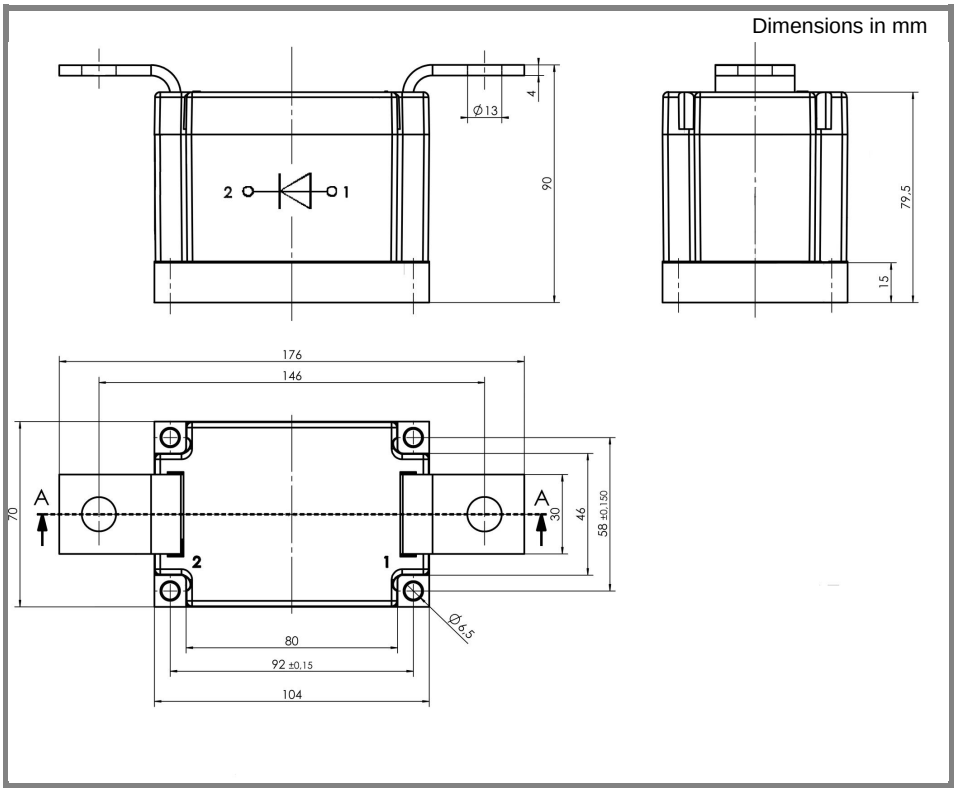


Fig. 16 Surge overload current vs. time



Case A82

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